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(54) METHOD FOR MANUFACTURING THIN FILM TRANSISTOR AND METHOD FOR MANUFACTURING LCD SUBSTRATE COMPRISING THE SAME

(57) Abstract:

PURPOSE: A method for manufacturing a thin film transistor and a method for manufacturing an LCD substrate comprising the same are provided to prevent corrosion of wiring or electrodes by restricting the generation of a galvanic cell.

CONSTITUTION: A method for manufacturing a thin film transistor comprises the steps of: forming a gate electrode on a substrate; forming a gate insulating layer on the gate electrode; forming an amorphous silicon layer on the gate insulating layer; forming a doped amorphous silicon layer thereon; forming a source electrode and a drain electrode thereon; and drying and etching the doped amorphous silicon layer. A method for manufacturing an LCD substrate comprising the same comprises the steps of: forming a gate wiring on an insulating substrate; forming a gate insulating layer thereon; forming an amorphous silicon layer on the gate insulating layer; forming a doped amorphous silicon layer thereon; forming a data wiring; and drying and etching the doped amorphous silicon layer.

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